

In the Abstract:

ABSTRACT OF THE DISCLOSURE

~~Method for the production of a plurality of optoelectronic semiconductor chips and~~
~~optoelectronic semiconductor chip~~

~~The invention relates to a~~ A method for the production of a plurality of optoelectronic semiconductor chips each having a plurality of structural elements with respectively at least one semiconductor layer. The method involves providing a chip composite base having a substrate and a growth surface. A mask material layer is formed on the growth surface, said mask material layer having a multiplicity of windows, most of which have an average extent of less than or equal to 1 μm . In this case, a mask material is chosen in such a way that a semiconductor material of the semiconductor layer that is to be grown in a later method step essentially cannot grow on said mask material or can grow in a substantially worse manner in comparison with the growth surface. Subsequently, semiconductor layers are deposited essentially simultaneously onto regions of the growth surface that lie within the windows. A further method step is singulation of the chip composite base with applied material to form semiconductor chips. ~~The invention additionally relates to an~~ An optoelectronic semiconductor component is produced according to the method.

~~Figure 2~~